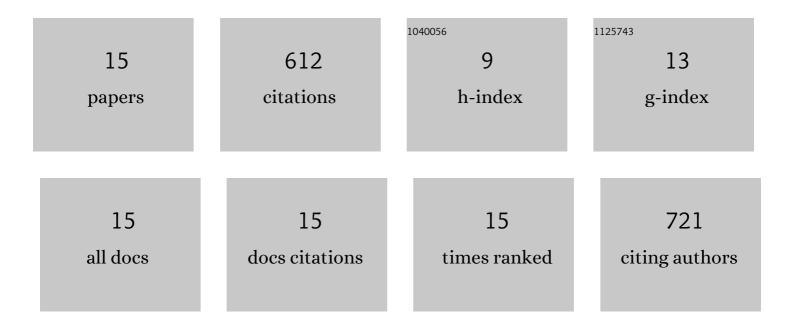
Pk Hurley

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/10732091/publications.pdf Version: 2024-02-01



DV HUDIEV

#	Article	IF	CITATION
1	Thermally activated analysis of LaSiOx/Si and GdSiOx/Si structures at cryogenic temperatures. Microelectronic Engineering, 2013, 109, 31-34.	2.4	1
2	Transport and interface states in high-κ LaSiOx dielectric. Microelectronic Engineering, 2011, 88, 1342-1345.	2.4	0
3	Determination of electron effective mass and electron affinity in HfO2 using MOS and MOSFET structures. Solid-State Electronics, 2009, 53, 438-444.	1.4	102
4	Scaling potential and MOSFET integration of thermally stable Gd silicate dielectrics. Microelectronic Engineering, 2009, 86, 1642-1645.	2.4	15
5	High-k-oxide/silicon interfaces characterized by capacitance frequency spectroscopy. Solid-State Electronics, 2008, 52, 1274-1279.	1.4	27
6	Gentle FUSI NiSi metal gate process for high-k dielectric screening. Microelectronic Engineering, 2008, 85, 2019-2021.	2.4	7
7	The influence of HfO2 film thickness on the interface state density and low field mobility of n channel HfO2/TiN gate MOSFETs. Microelectronic Engineering, 2007, 84, 1874-1877.	2.4	19
8	Navigation aids in the search for future high-k dielectrics: Physical and electrical trends. Solid-State Electronics, 2007, 51, 622-626.	1.4	124
9	Post deposition UV-induced O2 annealing of HfO2 thin films. Microelectronics Reliability, 2005, 45, 957-960.	1.7	4
10	Interface of ultrathin HfO2 films deposited by UV-photo-CVD. Thin Solid Films, 2004, 453-454, 203-207.	1.8	56
11	Investigation of TiO2-doped HfO2 thin films deposited by photo-CVD. Thin Solid Films, 2003, 428, 263-268.	1.8	50
12	Characterisation of HfO2 deposited by photo-induced chemical vapour deposition. Thin Solid Films, 2003, 427, 391-396.	1.8	35
13	Nanocrystalline TiO2 films studied by optical, XRD and FTIR spectroscopy. Journal of Non-Crystalline Solids, 2002, 303, 134-138.	3.1	163
14	Photo-Induced CVD of Tantalum Pentoxide Dielectric Films Using an Injection Liquid Source. Materials Research Society Symposia Proceedings, 1999, 567, 397.	0.1	9
15	Electrical Properties of High- <i>K</i> LaLuO ₃ Gate Oxide for SOI MOSFETs. Advanced Materials Research, 0, 276, 87-93.	0.3	Ο